Supporting Information

Mechano-Ferroelectric Coupling: Stabilization Enhancement and Polarization Switching in Bent AgBiP₂Se₆ Monolayer

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1. FE phase transition from $P \downarrow$ to $P \uparrow$ by bending in AgBiP₂Se₆ ribbons

Figure S1. Bending in AgBiP₂Se₆ nanoribbons. (a): The relaxation from initial AgBiP₂Se₆ nanoribbon with Ag atoms locating at the bottom layer (left panel) to the relaxed ribbons with Ag atoms moving upwards (right panel). Accordingly, the ferroelectric polarization is reversed. The orange balls represent the fixed edge Se atoms. (b): The energy difference ($\Delta E'$) between nanoribbons with negative (left panel) and positive (right panel) curvatures and nonperiodic flat AgBiP₂Se₆ nanoribbon. The insets are the bending directions for P \downarrow AgBiP₂Se₆ nanoribbons including up-bending (left) and down-bending (right). (c): The dipole moments (Debye) of the bent nanoribbons with various curvatures.

2. FE phase transition from $P \downarrow$ to $P \uparrow$ by bending in In₂Se₃ monolayer



Fig. S2. Structures with and without bending deformation in In_2Se_3 monolayer. The bending deformation in P \downarrow In₂Se₃ monolayer is resulted by the in-plane compressive strain of $\varepsilon = 0.08$, as labelled by black arrows. The blue and red arrows indicate the FE polarizations in In_2Se_3 monolayer. With bending load, the FE polarization in compressive area flips form P \downarrow to P \uparrow .

3. The size effect of ferroelectric bubble in AgBiP₂Se₆ monolayers



Fig. S3. Ferroelectric bubble with hights (*h*) in biaxially rippled AgBiP₂Se₆ monolayers. (a): 6×5 supercell with 4% biaxial strain; (b) : 6×6 supercell with 4% biaxial strain.